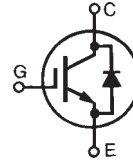


HiPerFAST™ IGBT with Diode

B2-Class High Speed IGBTs

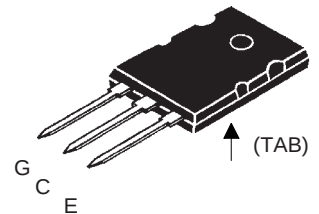
IXGK 50N60B2D1
IXGX 50N60B2D1

$V_{CES} = 600 \text{ V}$
 $I_{C25} = 75 \text{ A}$
 $V_{CE(sat)} = 2.0 \text{ V}$
 $t_{fi(typ)} = 65 \text{ ns}$

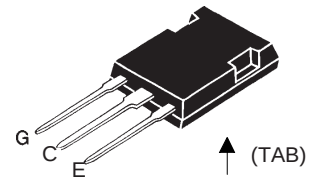


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (limited by leads)	75	A
I_{C110}	$T_C = 110^\circ\text{C}$	50	A
I_{F110}	$T_C = 110^\circ\text{C}$ (50N60B2D1 Diode)	38	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	200	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10 \Omega$ Clamped inductive load @ $V_{CE} \leq 600 \text{ V}$	$I_{CM} = 80$	A
P_c	$T_C = 25^\circ\text{C}$	400	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque, TO-264	1.13/10 Nm/lb.in.	
Weight	TO-264	10	g
	PLUS247	6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

**TO-264
(IXGK)**



**PLUS247
(IXGX)**



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- High frequency IGBT and anti-parallel FRED in one package
- High current handling capability
- MOS Gate turn-on for drive simplicity
- Fast Recovery Epitaxial Diode (FRED) with soft recovery and low I_{RM}

Applications

- Switch-mode and resonant-mode power supplies
- Uninterruptible power supplies (UPS)
- DC choppers
- AC motor speed control
- DC servo and robot drives

Advantages

- Space savings (two devices in one package)
- Easy to mount with 1 screw

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$			600 μA
	$V_{GE} = 0 \text{ V}$			5 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = 40 \text{ A}, V_{GE} = 15 \text{ V}$	1.6	2.0	V
	Note 1	1.5		V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$I_C = 40\text{ A}$; $V_{CE} = 10\text{ V}$, Note 1	40	55	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		3500	pF
C_{oes}			220	pF
C_{res}			50	pF
Q_g	$I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		140	nC
Q_{ge}			23	nC
Q_{gc}			44	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 480\text{ V}$, $R_G = R_{off} = 5.0\ \Omega$		18	ns
t_{ri}			25	ns
$t_{d(off)}$			190	ns
t_{fi}			65	ns
E_{off}		0.55	0.85	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 480\text{ V}$, $R_G = R_{off} = 5.0\ \Omega$		18	ns
t_{ri}			25	ns
E_{on}			0.9	mJ
$t_{d(off)}$			290	ns
t_{fi}			140	ns
E_{off}			1.55	mJ
R_{thJC}			0.31	K/W
R_{thCK}		0.15		K/W

Reverse Diode (FRED)

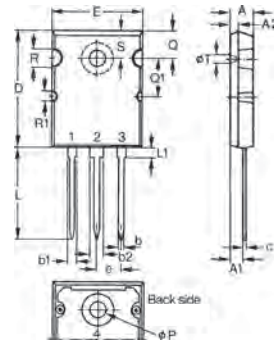
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = 60\text{ A}$, $V_{GE} = 0\text{ V}$, Note 1 $T_J = 150^\circ\text{C}$			2.1 V
I_{RM}	$I_F = 60\text{ A}$, $V_{GE} = 0\text{ V}$, $-di_F/dt = 100\text{ A}/\mu\text{s}$, $T_J = 100^\circ\text{C}$ $V_R = 100\text{ V}$			8.3 A
t_{rr}	$I_F = 1\text{ A}$; $-di/dt = 200\text{ A/ms}$; $V_R = 30\text{ V}$		35	ns
R_{thJC}				0.65 K/W

Note 1: Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$

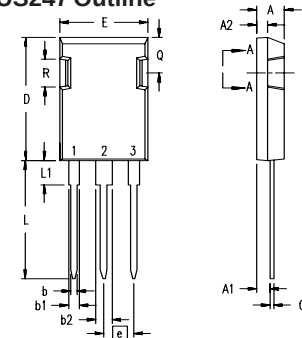
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

TO-264 Outline


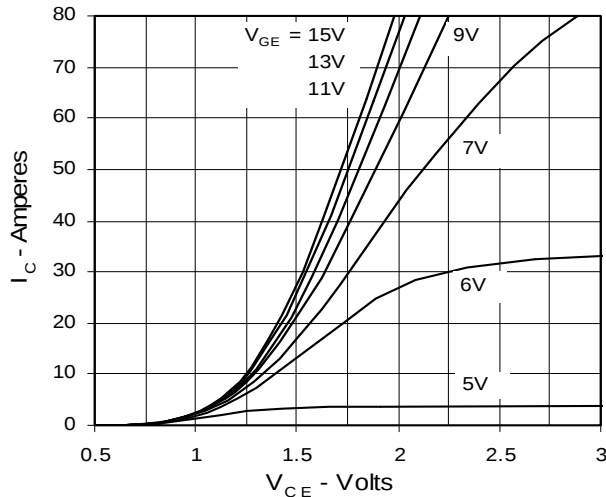
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS247 Outline


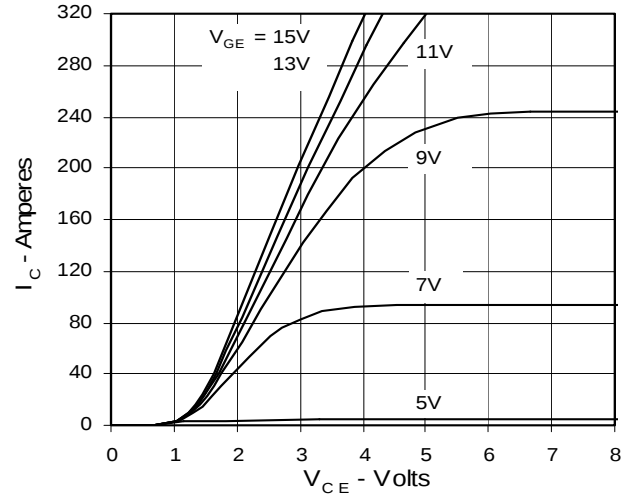
Terminals:
 1 - Gate
 2 - Drain (Collector)
 3 - Source (Emitter)
 4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
b2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

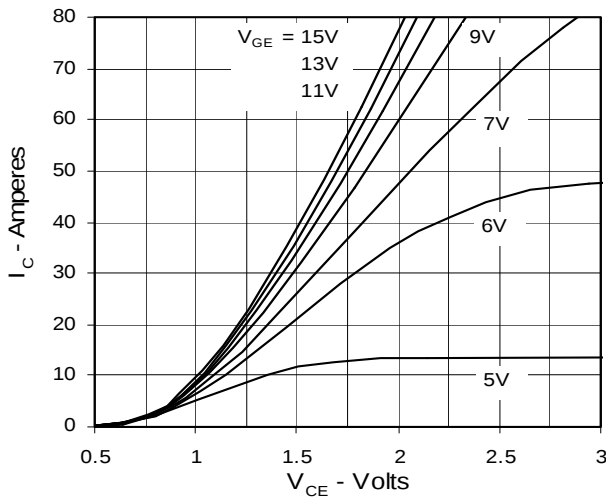
**Fig. 1. Output Characteristics
@ 25 Deg. C**



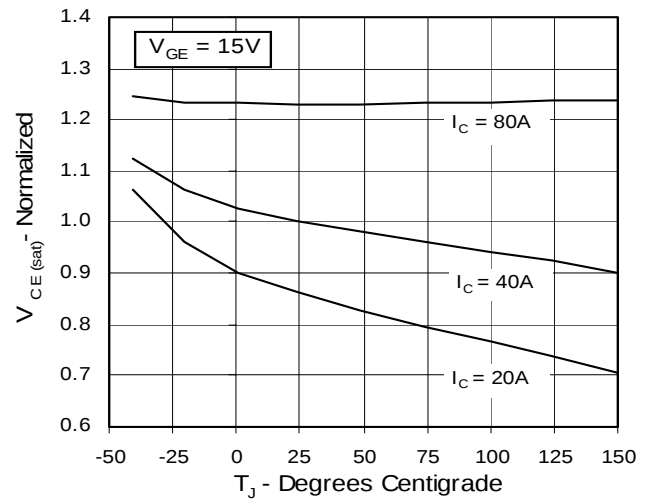
**Fig. 2. Extended Output Characteristics
@ 25 deg. C**



**Fig. 3. Output Characteristics
@ 125 Deg. C**



**Fig. 4. Dependence of $V_{CE(sat)}$ on
Temperature**



**Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter voltage**

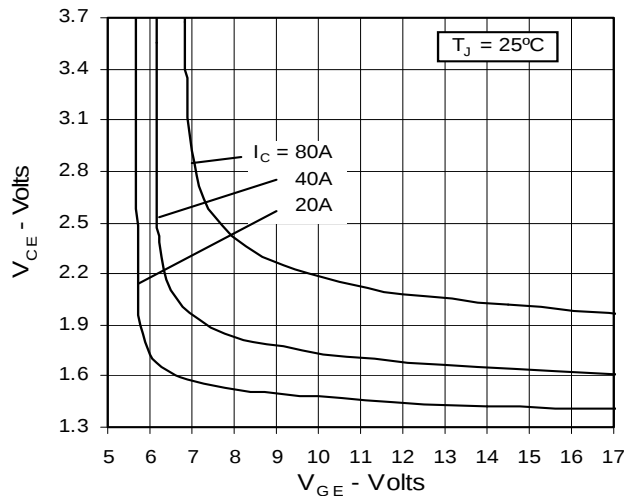


Fig. 6. Input Admittance

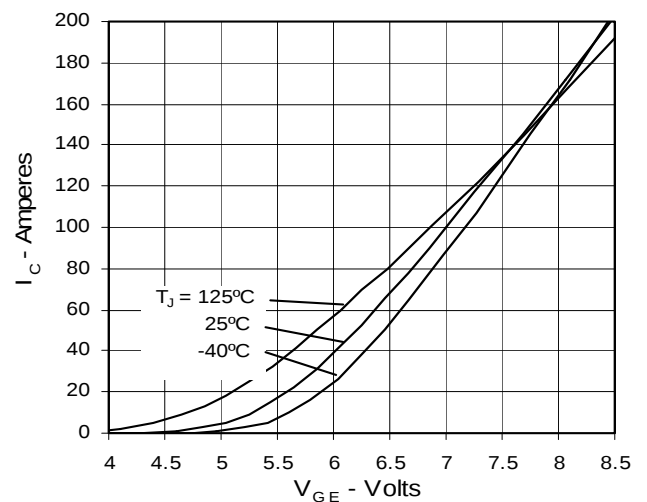


Fig. 7. Transconductance

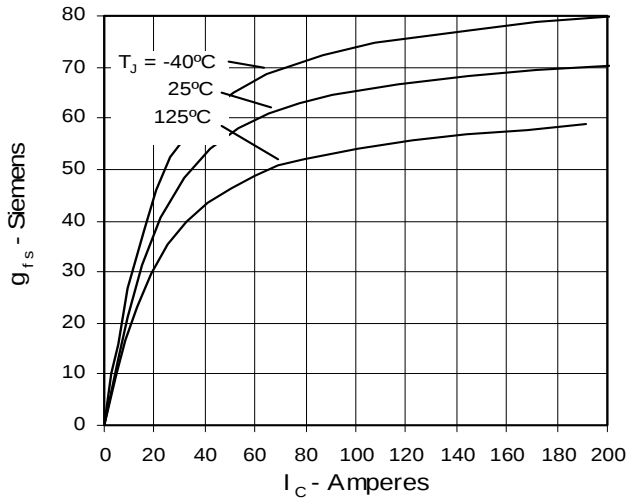


Fig. 8. Dependence of Turn-Off Energy on R_G

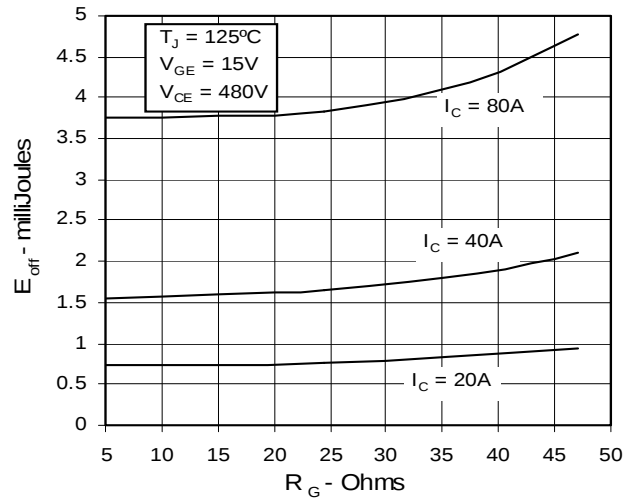


Fig. 9. Dependence of Turn-Off Energy on I_C

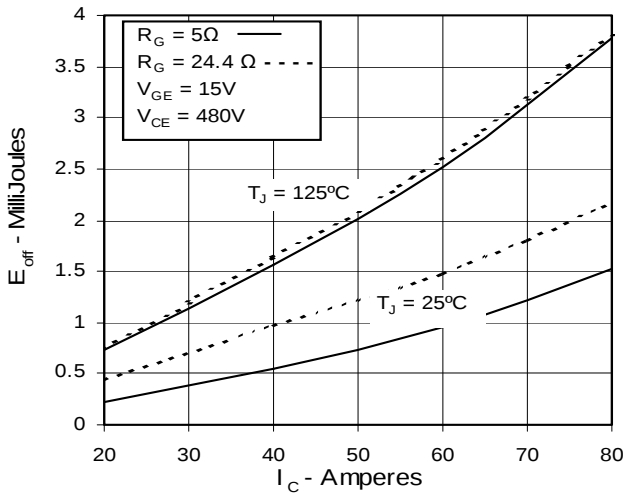


Fig. 10. Dependence of Turn-Off Energy on Temperature

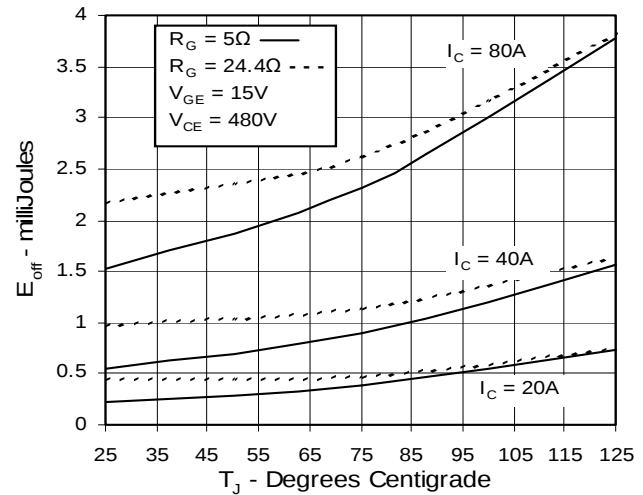


Fig. 11. Dependence of Turn-Off Switching Time on R_G

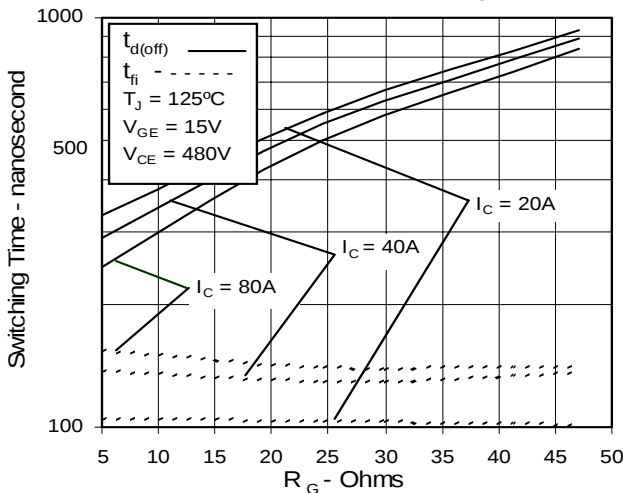
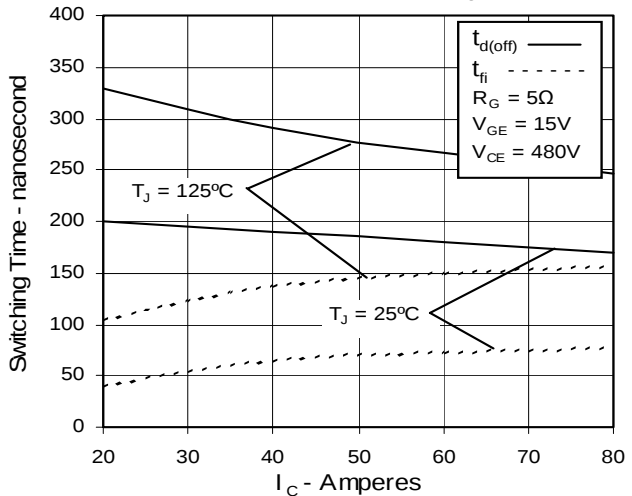


Fig. 12. Dependence of Turn-Off Switching Time on I_C



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4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

Fig. 13. Dependence of Turn-Off Switching Time on Temperature

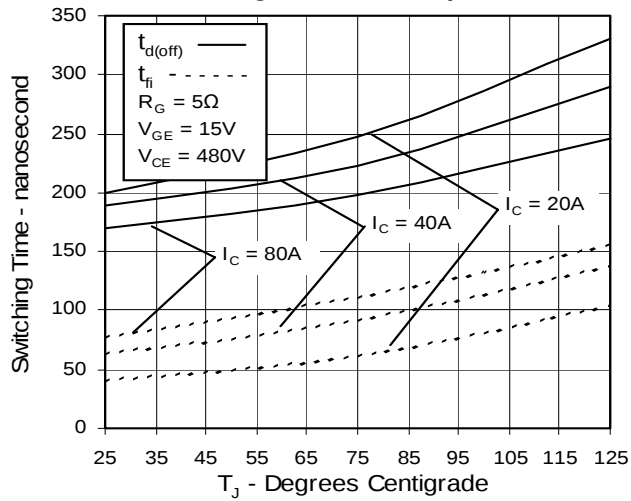


Fig. 14. Reverse-Bias Safe Operating Area

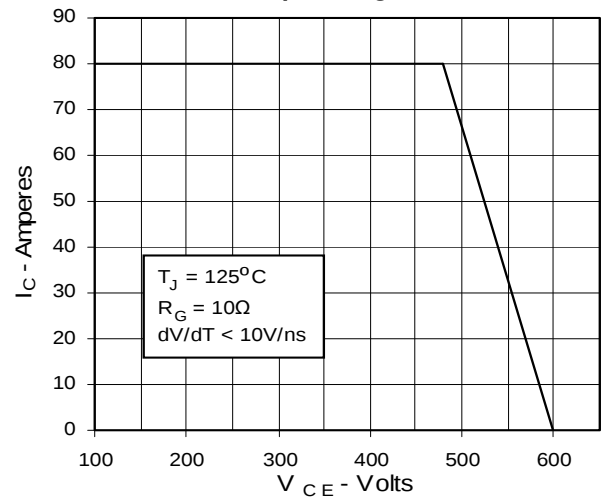


Fig. 15. Gate Charge

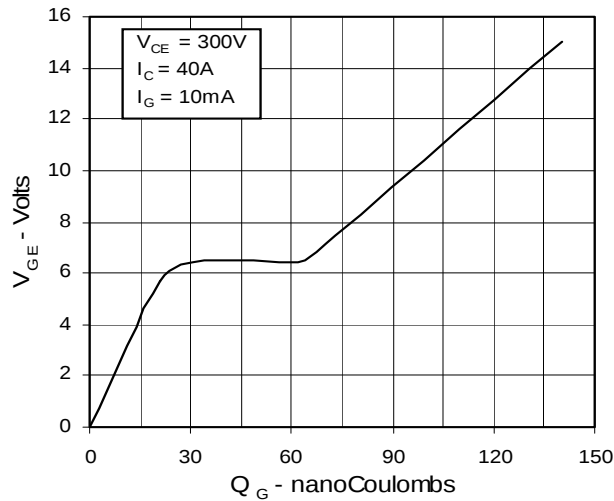


Fig. 16. Capacitance

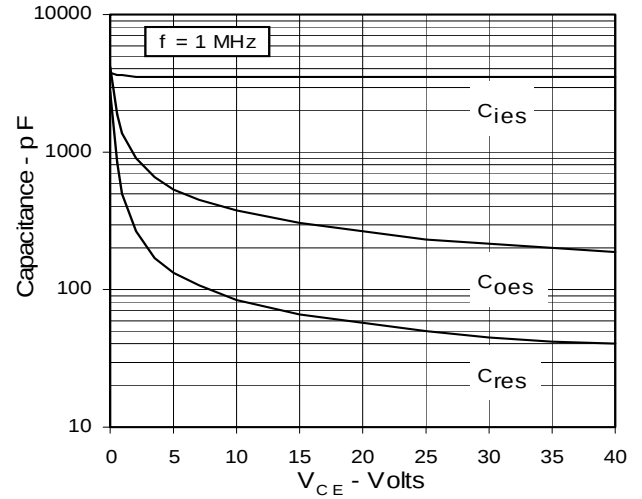
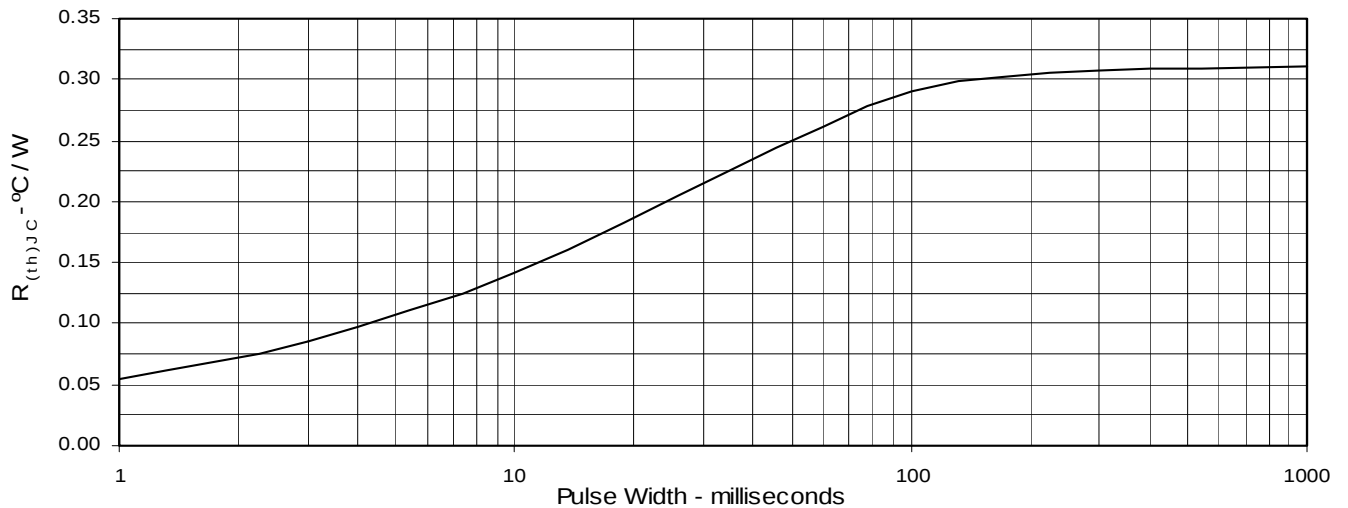


Fig. 17. Maximum Transient Thermal Resistance



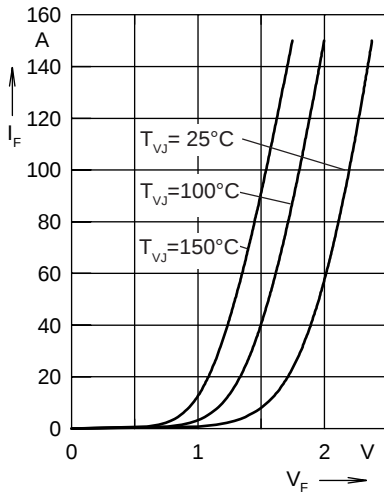


Fig. 18. Forward current I_F versus V_F

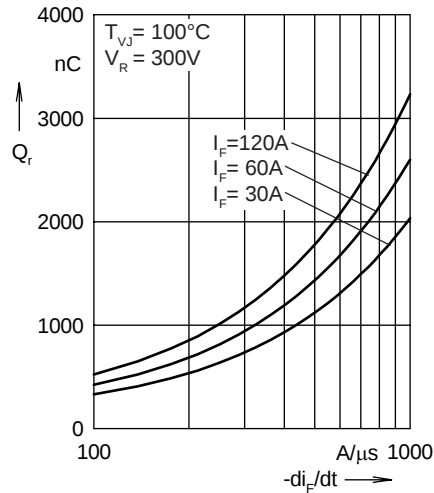


Fig. 19. Reverse recovery charge Q_r versus $-di_F/dt$

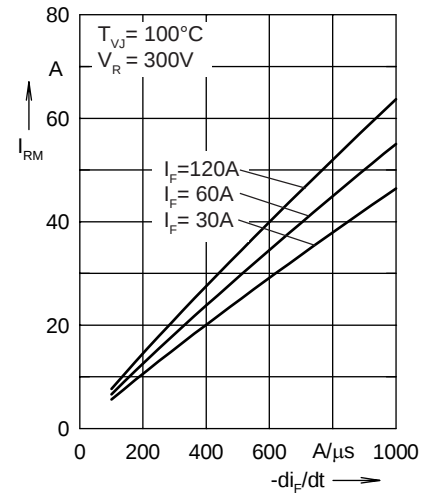


Fig. 20. Peak reverse current I_{RM} versus $-di_F/dt$

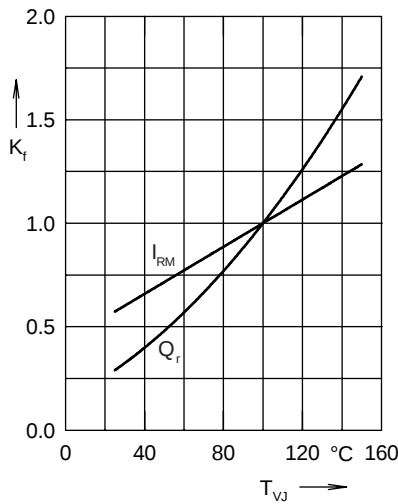


Fig. 21. Dynamic parameters Q_r , I_{RM} versus T_{VJ}

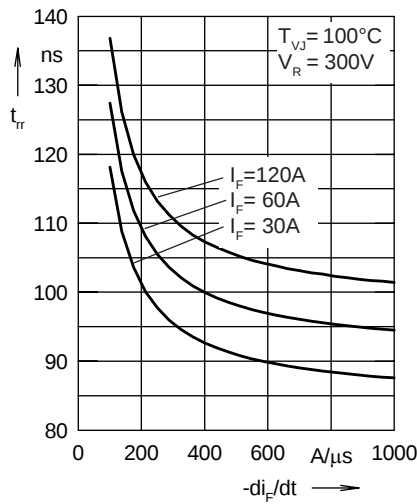


Fig. 22. Recovery time t_{rr} versus $-di_F/dt$

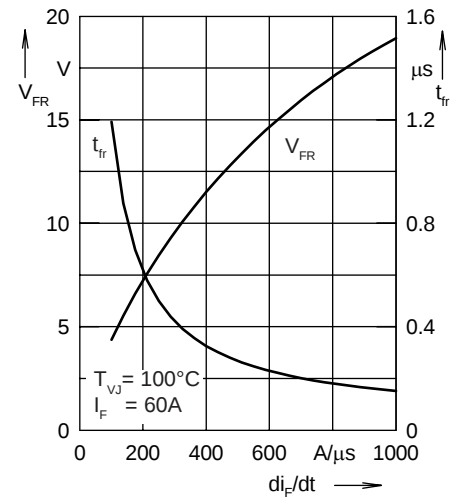


Fig. 23. Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.324	0.0052
2	0.125	0.0003
3	0.201	0.0385

Note: Fig. 18 through Fig. 23 show typical values

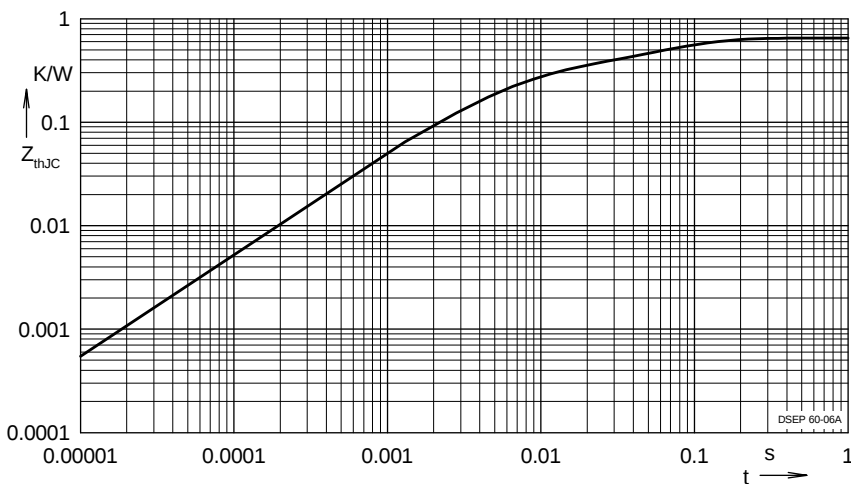


Fig. 24. Transient thermal resistance junction to case

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